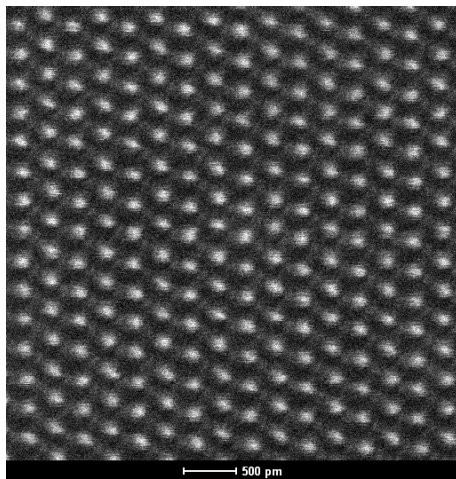


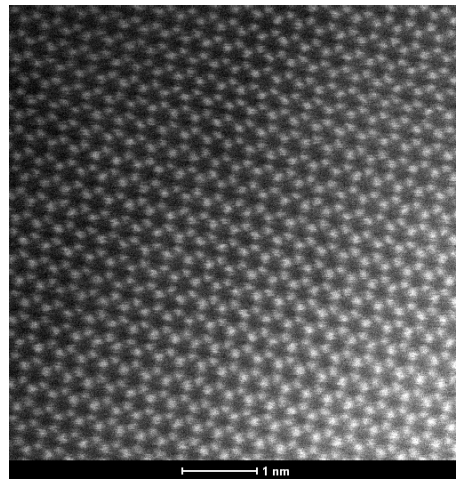
Atomic structure characterization of PEALE semiconductor by using HRSTEM



Fig. 1. In-situ plasma enhanced atomic layer etching system (PEALE).



(1) GaN



(2) MoS₂

Fig.2. Atomic structure images of (1)GaN and (2)MoS₂ by using aberration-corrected scanning transmission electron microscope.